Silicon NPN Power Transistors

2SD2333

DESCRIPTION

- With TO-3PML package
- High breakdown voltage
- Built-in damper diode

APPLICATIONS

- Color TV horizontal deflection output applications

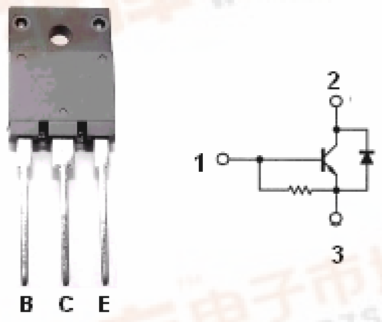

Fig.1 simplified outline (TO-3PML) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		5	A
I_{BM}	Base current-peak		2.5	A
P_C	Collector power dissipation	T_C=25℃	80	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA; I_B=0	800			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=200mA , I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=4A ;I_B=0.8A			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=4A; I_B=0.8A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=500V; I_E=0			10	μA
h_{FE}	DC current gain	I_C=1A ; V_{CE}=5V	8			
V_F	Diode forward voltage	I_F=5A			2.0	V

PACKAGE OUTLINE

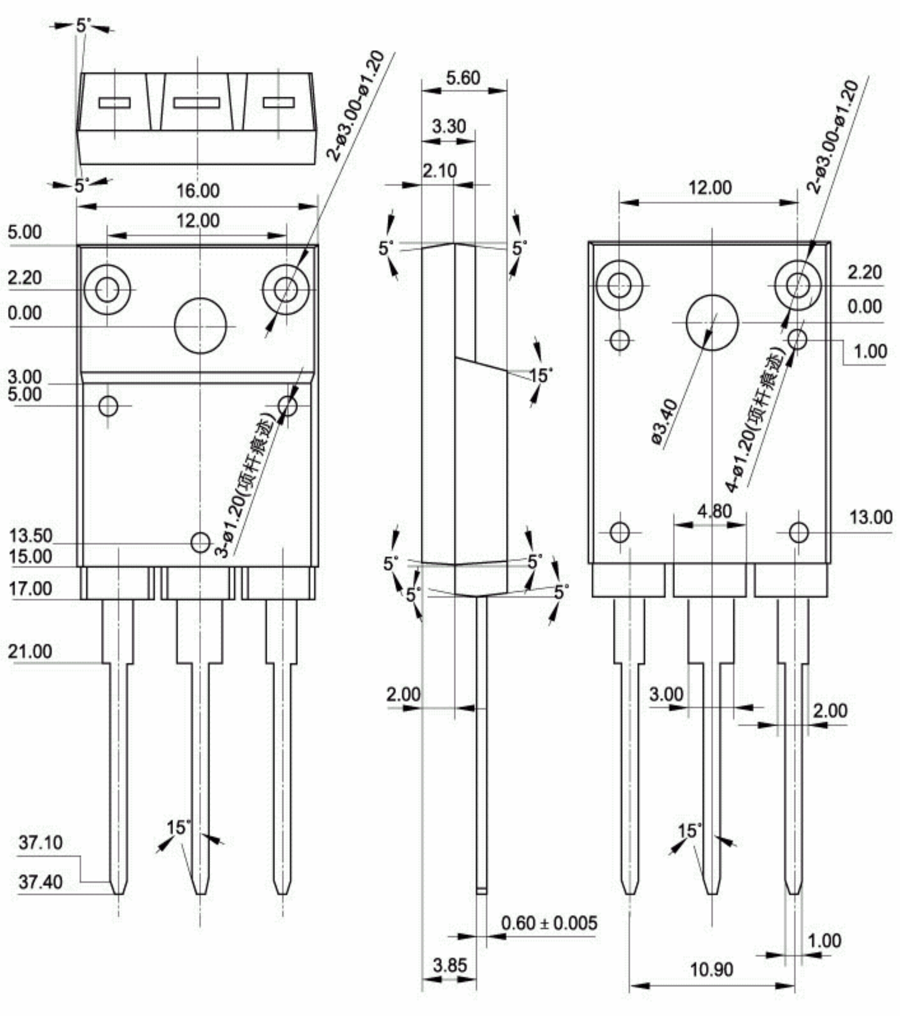

Fig.2 Outline dimensions